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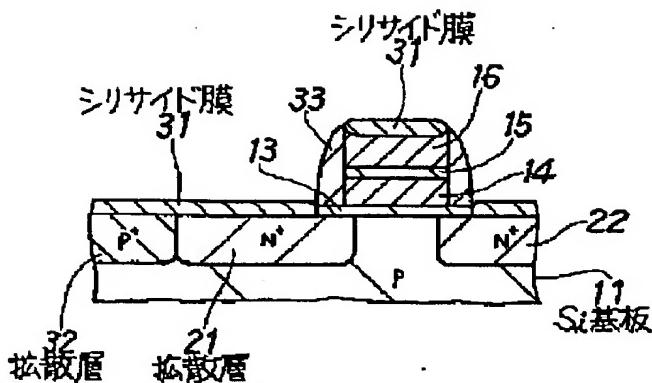
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APPLICANT : SONY CORP;

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TITLE : SEMICONDUCTOR DEVICE



ABSTRACT : PURPOSE: To realize fine patterning and high density while sustaining a diffusion layer, having conductivity type opposite to that of a semiconductor substrate, at same potential as the semiconductor substrate.

CONSTITUTION: N⁺ type and P⁺ type diffusion layers 21, 32 are provided on an Si substrate 11 and a silicide film 31 spreads while touching the surfaces of the diffusion layers 21, 32 thus equalizing the potential of the diffusion layer 21 and the Si substrate 11 through the diffusion layer 32 and the silicide film 31. Since no contact hole is required in the diffusion layers 21, 32 nor any wiring is required to be connected through a contact hole with the diffusion layers 21, 32, no region is required for the contact hole or the wiring.

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